

Gs/s Analog-to-Digital Converters in sub-16nm Process Technologies



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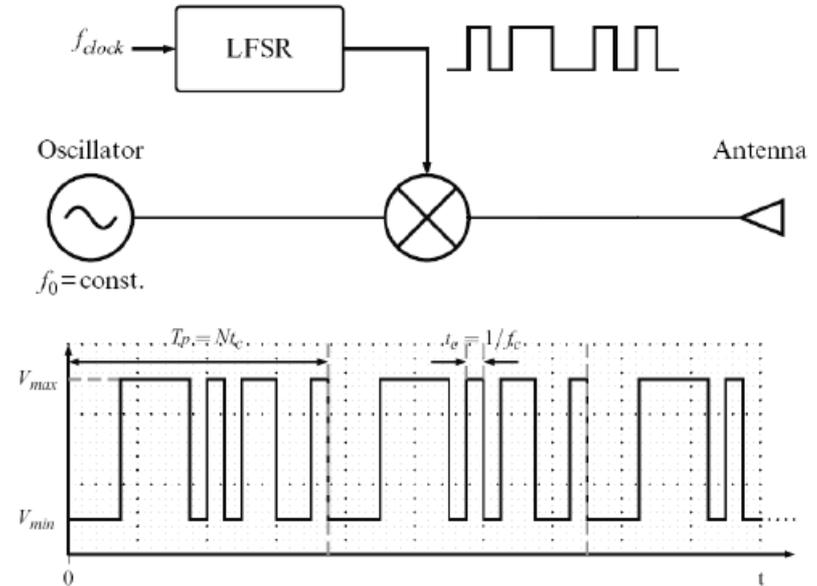
SECURE CONNECTIONS
FOR A SMARTER WORLD

- The need for (and challenges of) Gs/s ADCs in sub-16nm process technologies
- Status → where are we now? where to we need to go?
- Example implementatons

Digitally Modulated Radar (DMR)

What is it?

- In a DMR-based automotive radar system, a (digital) Pseudo-Random Binary Sequence (PRBS) is used to modulate the phase of a ($\sim 79\text{GHz}$) continuous-wave signal which is then transmitted as the range finding signal.
- The PRBS is designed to enable both unambiguous range (sequence length) and range resolution (pulse width \rightarrow bandwidth) while also (potentially) providing excellent immunity to interference.
- The reflected signal is then received and processed (i.e. correlated and accumulated) to determine the range and velocity (FFT) of the target.

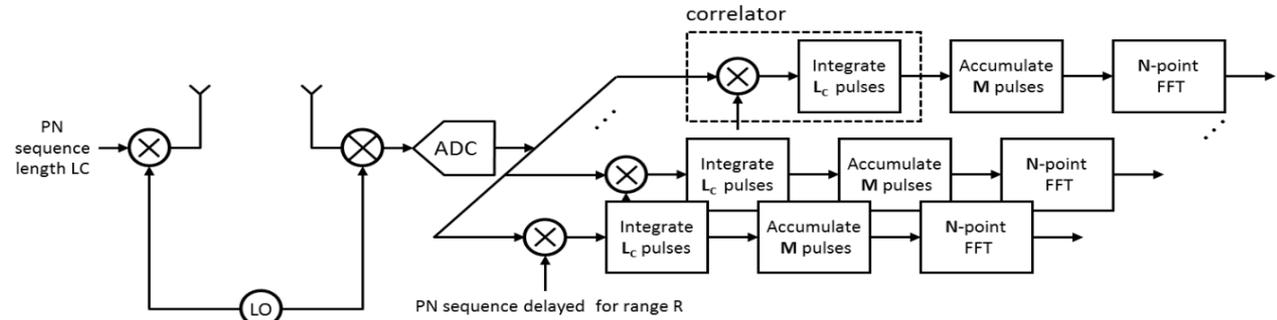


simplified DMR transmitter and PRBS diagrams*

Digitally Modulated Radar (DMR)

Why is it good?

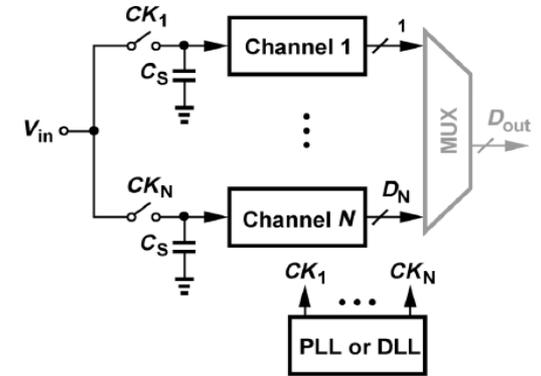
- Waveform generation is very simple → no fast-settling, highly-linear frequency synthesizers are required as with FMCW-based radar systems
- Since the PRBS codes that are used to modulate the carrier are designed to be essentially random and to have nearly perfect correlation properties, excellent range resolution and **potential** immunity to interference can be achieved.
- MIMO (Multiple-Input, Multiple-Output) and Beamforming techniques can be readily applied to a DMR-based system to improve range and angular resolution respectively.
- Receiver is predominantly digital (see diagram below) and requires extensive high-speed signal processing (e.g. correlator, accumulator, FFT, etc.), and provides significant (~ 70 +dB) of processing gain and can also be readily implemented in a FinFET process technology.



Digitally Modulated Radar (DMR)

Is there a catch? (...there's always a catch)

- Since the achievable performance/accuracy of a DMR-based automotive radar is directly proportional to the bandwidth (more is better) of the range finding signals, the ADC that samples the received PRBS signals is required to have very-wide bandwidth (e.g. 2GHz to 5GHz depending upon the system requirements and implementation compared to 10MHz to 20MHz for a FMCW-based system) and correspondingly high sample rate (4Gs/s to 10Gs/s)...**but that's why DMR-based radars are so interesting!**
- A (~10-b) time-interleaved ADC architecture with associated clock issues (e.g. jitter, skew, etc.), low supply voltage, etc. will almost certainly be required...
- Because the Gs/s ADC output is correlated in real time with the PBRS that was used to modulate the 79GHz carrier phase, extremely high-speed (GHz) digital signal processing is also needed...



→ **ADC and signal processing should both be implemented in the same sub-16nm technology!**

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ADC benchmarking → background

- analog-to-digital converters (ADCs) are (almost) universally compared based upon figures of merit (FoM) of one kind or another.
- for high-speed ADCs, the most commonly used is the *Walden FoM (a.k.a. EQ)

$$EQ = \frac{P}{2^{ENOB} 2F_{BW}}$$

where P is power, ENOB is the effective number of bits, and F_{BW} is the input bandwidth

- EQ is essentially a measure of the energy per conversion step (in pico-Joules (pJ))
→ lower is better for this FoM
- the following charts plot EQ versus ENOB and EQ versus F_{BW} for a number of university designed ADCs and a number of industry designed ADCs

* R. H. Walden, "Analog-to-digital converter survey and analysis," IEEE J. Sel. Areas Commun., Vol. 17, no. 4, pp. 530-550, 1999



...a word (or two) about FoMs for ADCs used in automotive applications:

critical ADC requirements in rank order (especially for automotive applications):

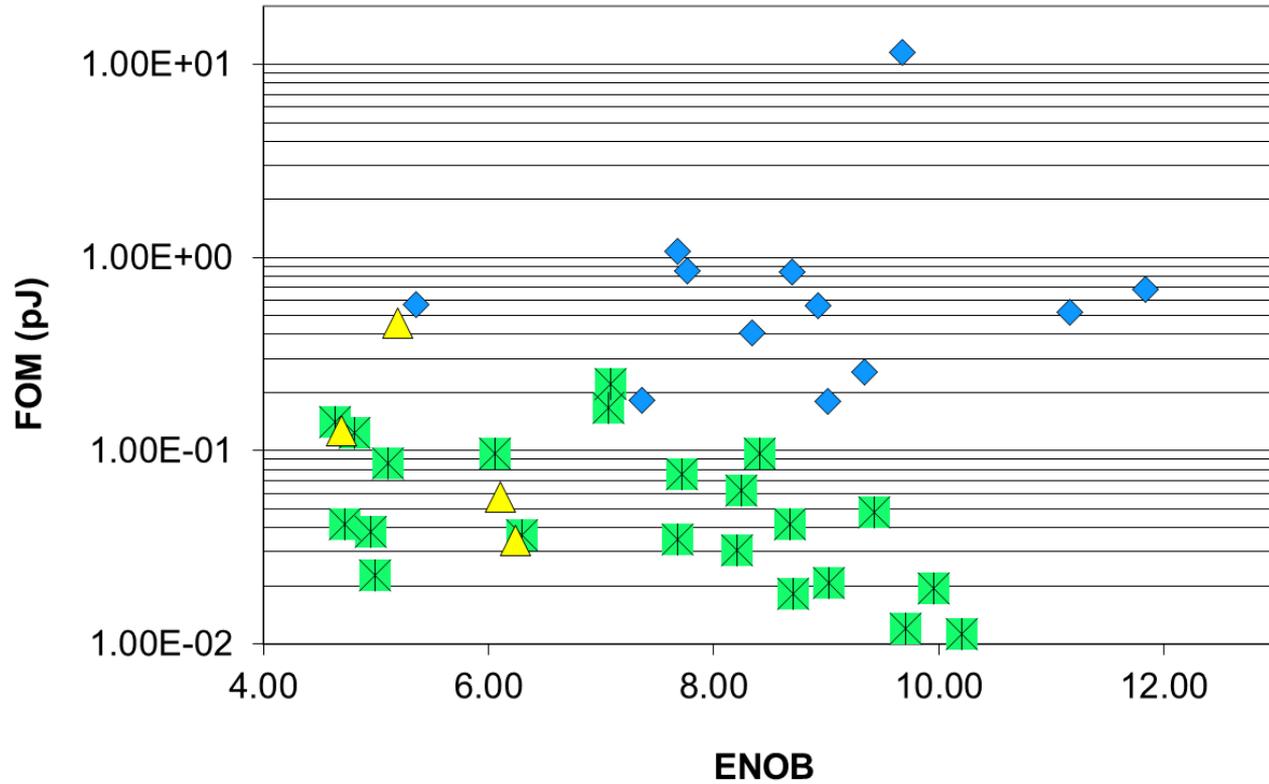
- 1. does the ADC actually work as required in the application? (specifications like IFDR, OEV, ADV, etc. do NOT show up in an any FoM (EVER))**
- 2. is the ADC manufacturable in high-volume production with automotive temperature ranges and reliability requirements?**
- 3. is the ADC a cost effective solution for the application?**

→ if the first 3 requirements are met – then FoMs can be considered as a basis of ADC comparison

→ ADC performance is widely/aggressively published in the IEEE literature (i.e. ISSCC, VLSI Symposium, etc.)



EQ vs ENOB for Gs/s ADCs (university vs industrial)

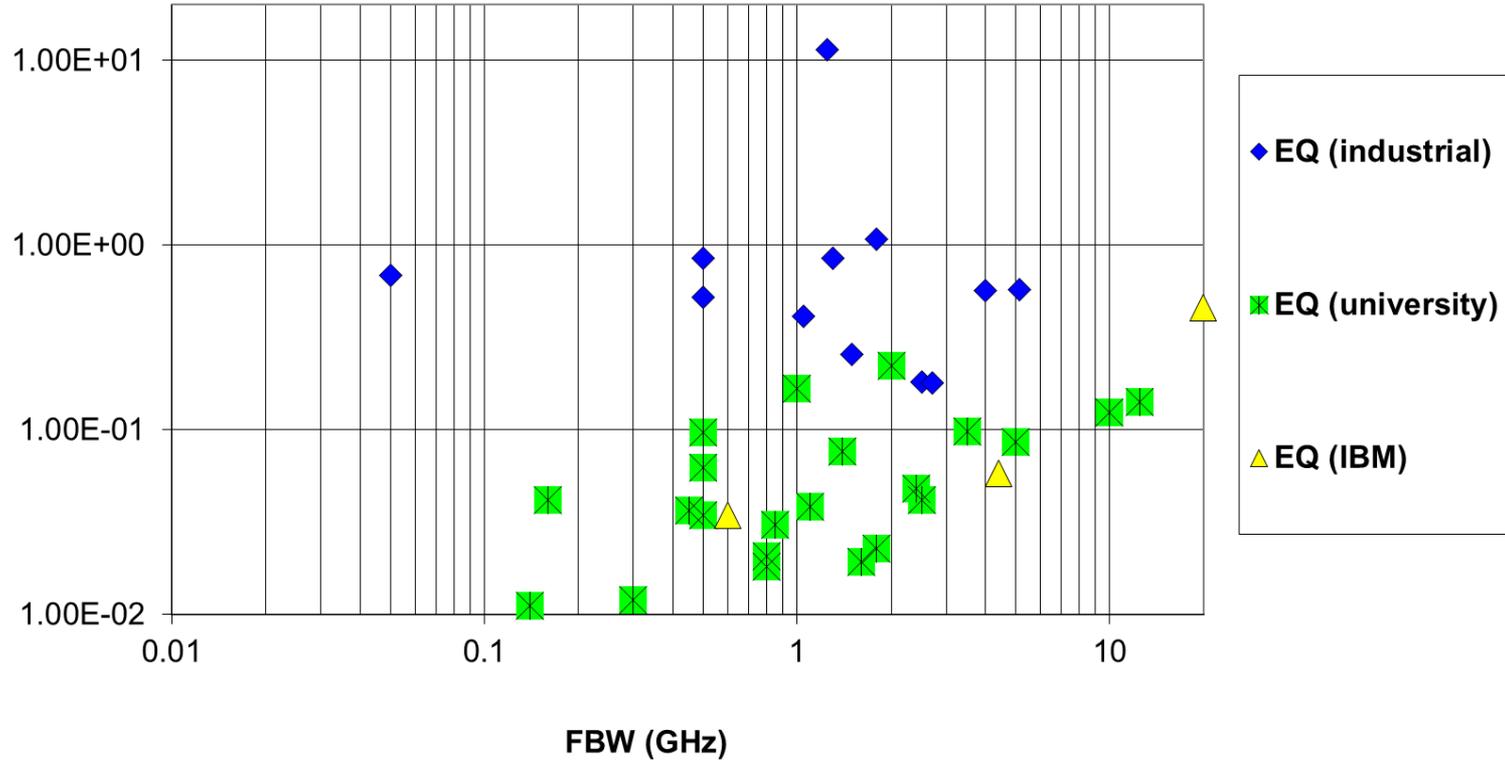


$$EQ = \frac{P}{2^{ENOB} 2F_{BW}}$$

- ◆ EQ (industrial)
- ⊠ EQ (university)
- ▲ EQ (IBM)

EQ vs F_{BW} for Gs/s ADCs (university vs. industrial)

$$EQ = \frac{P}{2^{ENOB} 2F_{BW}}$$



Summary/Concerns:

- Universities are producing overwhelming majority of the published Gs/s ADCs with the best FoMs but...
 - only 3 of the published ADCs shown have been implemented in 16nm and none in sub-16nm technologies
 - there are a few in 28nm, but most are 40nm or higher
 - universities focus primarily on FoM in order get their research published
- Industry needs sub-16nm Gs/s ADCs with specific application-based requirements (e.g. low cost, high-yield, IFDR, etc.) **and** excellent FoMs but...
 - from Marcel Pelgrom* "...industry contributions (to ISSCC) have dropped to 30%, and in absolute numbers, the 1974 level has been passed - in the downward direction"
 - Why? because industrial companies working on their own are typically more short-term financially driven and are usually not willing/able to invest sufficiently in long-term internal research

*Marcel Pelgrom, "Industry Research," IEEE Solid-State Circuits Magazine, Fall 2019



- **The need for (and challenges of) Gs/s ADCs in sub-16nm process technologies**
- **Status → where are we now? where to we need to go?**
- **Example implementatons:**
 - **time-interleaved**
 - **time-based**
 - **hybrid**

time-interleaved example*: 24 to 72Gs/s, 8-b ADC in 14-nm CMOS

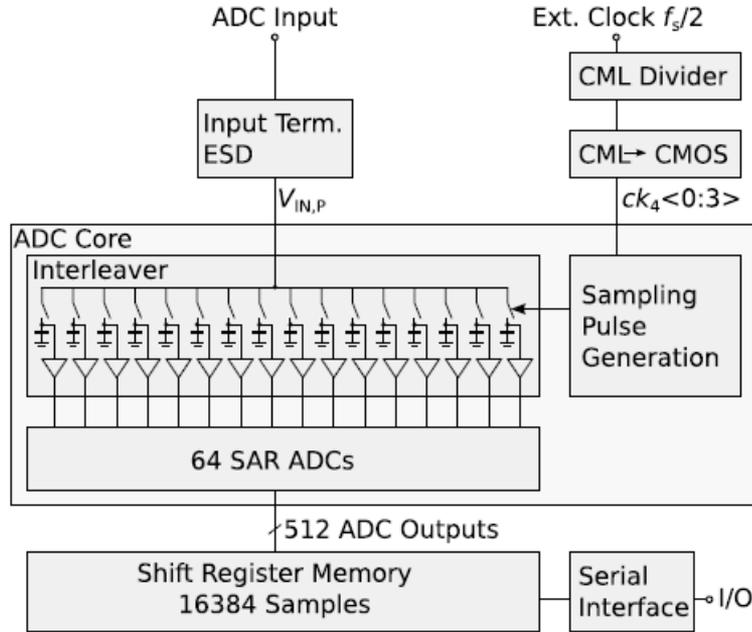


Fig. 1. ADC overview.

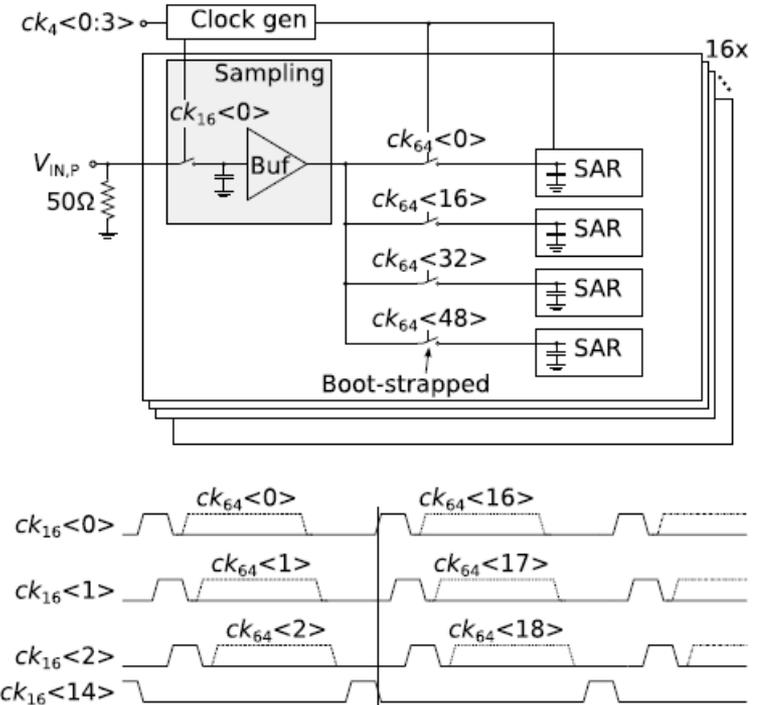


Fig. 2. Overview of the interleaver with input clock waveforms.

*L. Kull, et al, "A 24–72-GS/s 8-b Time-Interleaved SAR ADC With 2.0–3.3-pJ/Conversion and >30 dB SNDR at Nyquist in 14-nm CMOS FinFET, IEEE JSSC Dec. 2018



measured performance:

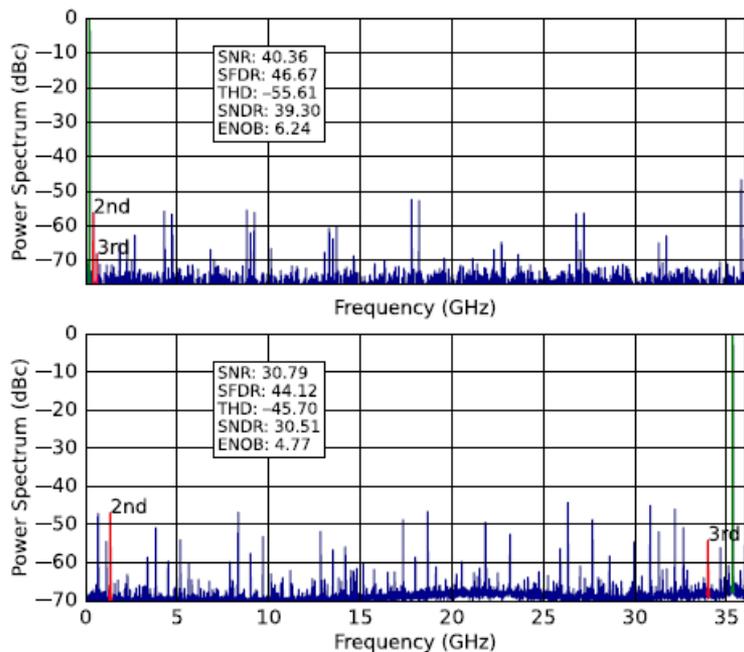


Fig. 15. Power spectrum density at low and high input frequencies, both measured at 72 GS/s.

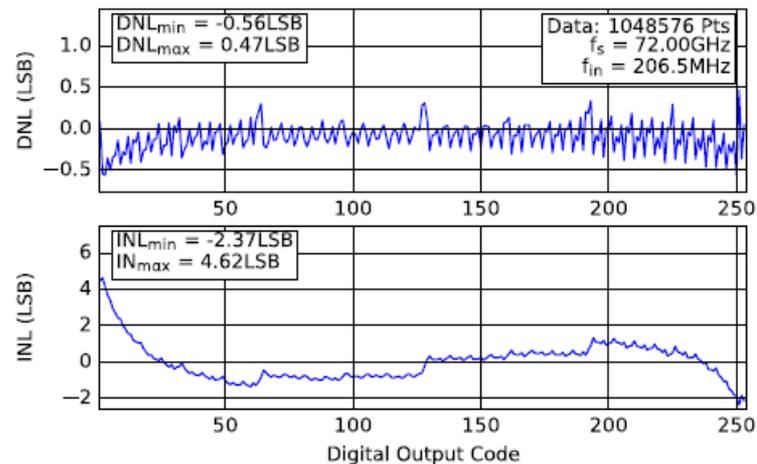


Fig. 16. INL and DNL.

time-based example*: 1Gs/s, 2.3mW, 8-b ADC in 65nm CMOS

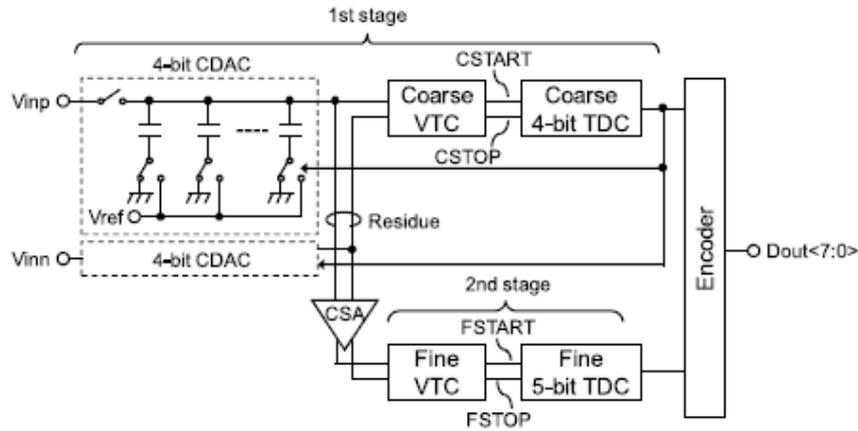
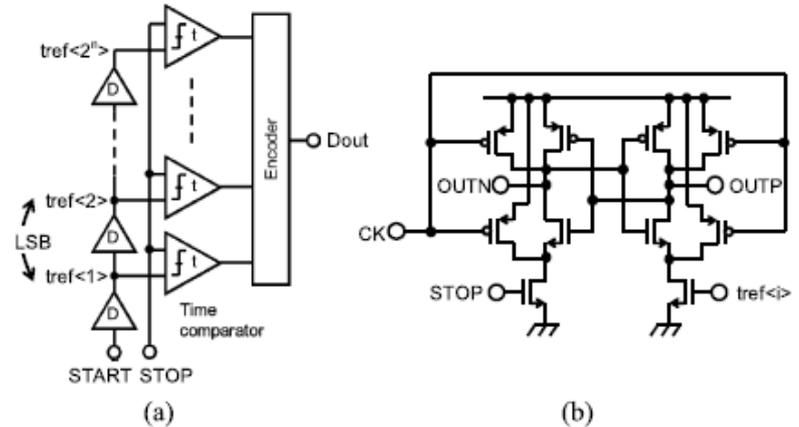


Fig. 6. Schematic of 8-bit fully time-based two-step ADC.



3. Schematic of (a) time-domain quantizer and (b) time comparator.

*K. Ohhata, "A 2.3-mW, 1-GHz, 8-bit Fully Time-Based Two-Step ADC Using a High-Linearity Dynamic VTC," IEEE JSSC, July 2019



measured performance:

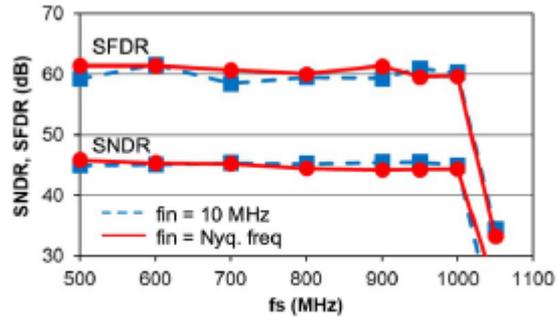


Fig. 29. Measured sampling frequency dependences of SNDR and SFDR.

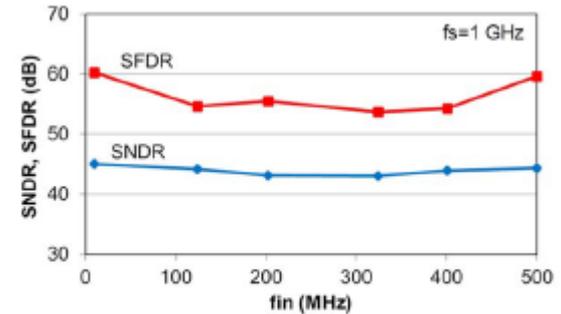
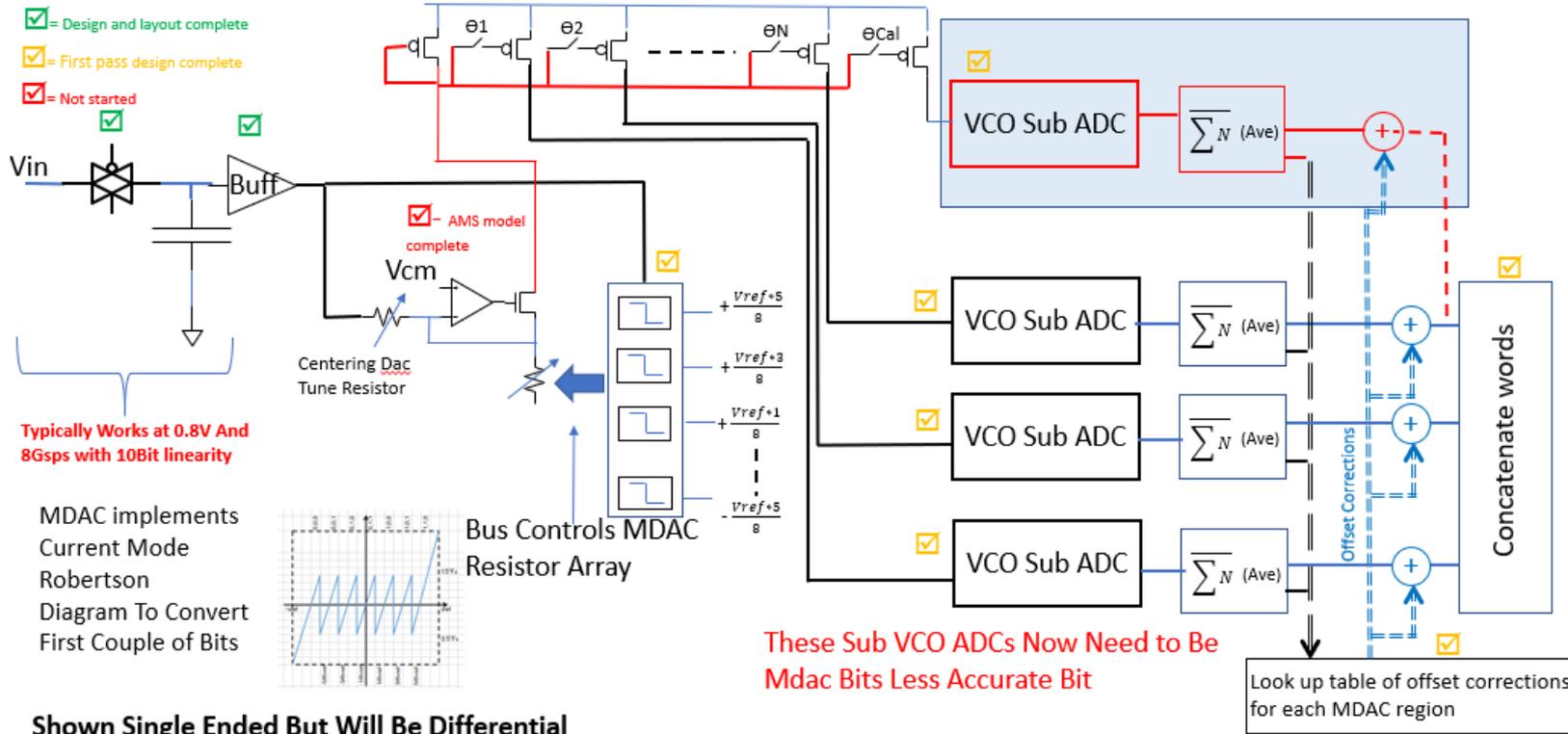


Fig. 30. Measured input frequency dependences of SNDR and SFDR.

*another possible approach...4-8Gs/s ADC in 16nm

All Supplies To Be Regulated to 0.8-0.9V

- = Design and layout complete
- = First pass design complete
- = Not started



conclusions and recommendations:

- While progress is being made, there is still plenty of work to be done...
- Industry needs collaborate closely with university researchers through internal/external funding sources
- Industry needs to collaborate CLOSELY with the university researchers to ensure that the developed ADCs meet all requirements and NOT just FoMs
- Universities (and IEEE conferences) need to be willing to accept an ADC with possibly a slightly worse FoM but that actually works...
- Industry/other funding sources need to provide university researchers with regular/consistent access to sub-16nm process technologies